

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In the Patent Application of

Takashi NOGUCHI et al.

Serial No.: To Be Assigned

Art Unit: 2813

Filed: January 8, 2004

Examiner: Jack S. J. Chen

For: METHOD OF FORMING N-AND P-CHANNEL  
FIELD EFFECT TRANSISTORS ON THE SAME  
SILICON LAYER HAVING A STREAM EFFECT

**INFORMATION DISCLOSURE STATEMENT UNDER 37 CFR §1.56**

**BOX PATENT APPLICATION**

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Sir:

Submitted herewith on Form PTO/SB/08A is a listing of documents known to Applicant cited by or submitted to the U.S. Patent and Trademark Office (USPTO) in parent application No. 09/048,288; filed on March 26, 1998 in order to comply with Applicant's duty of disclosure pursuant to 37 CFR §1.56. The relevance of these documents is explained in the parent application. As provided in 37 CFR 1.98(d), copies of the document are not provided since they were previously cited by or submitted to the Patent Office in the parent application.

Since this Information Disclosure Statement is being filed in compliance with 37 CFR § 1.97(b) before an initial action, no fee is required in connection with its filing.

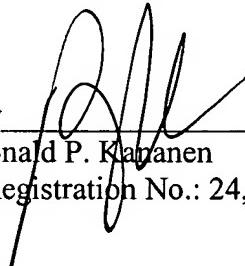
The submission of any document herewith, which is not a statutory bar, is not intended as an admission that such document constitutes prior art against the claims of the present application or that such document is considered material to patentability as defined in 37 CFR §1.56(b). Applicant does not waive any rights to take any action which would be appropriate to antedate or otherwise

remove as a competent reference any document which is determined to be a *prima facie* prior art reference against the claims of the present application.

Applicant respectfully requests that the listed documents be considered by the Examiner and formally be made of record in the present application and that an initialed copy of Form PTO/SB/08A be returned in accordance with MPEP §609.

Respectfully submitted,

By \_\_\_\_\_  
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Dated: January 8, 2004

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Substitute for form 1449/PTO				Complete if Known	
<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b> <i>(use as many sheets as necessary)</i>				Application Number	To Be Assigned
				Filing Date	January 8, 2004
				First Named Inventor	Takashi NOGUCHI et al.
				Art Unit	2813
				Examiner Name	Jack S. J. Chen
Sheet	1	of	1	Attorney Docket Number	SON-1285/DIV

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. <sup>1</sup>	Document Number Number-Kind Code <sup>2</sup> (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
AA	5,155,571	10/13/1992	Wang et al.		
AB	5,241,197	08/31/1993	Murakami et al.		
AC	5,665,616	08/09/1997	Kimura et al.		
AD	5,998,807	12/07/1999	Lustig et al.		
AE	US2002/0011617 A1	01/31/2002	Kubo et al.		

FOREIGN PATENT DOCUMENTS					
Examiner Initials*	Cite No. <sup>1</sup>	Foreign Patent Document Country Code <sup>3</sup> -Number <sup>4</sup> -Kind Code <sup>5</sup> (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
BA					T <sup>6</sup>
BB					T
BC					T
BD					
BE					

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. <sup>1</sup>Applicant's unique citation designation number (optional). <sup>2</sup>See Kinds Codes of USPTO Patent Documents at [www.uspto.gov](http://www.uspto.gov) or MPEP 901.04. <sup>3</sup>Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). <sup>4</sup>For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the application number of the patent document. <sup>5</sup>Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. <sup>6</sup>Applicant is to place a check mark here if English language Translation is attached.

NON PATENT LITERATURE DOCUMENTS					
Examiner Initials	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.			
	CA	K. Ismail et al., "Electron transport properties of Si/SiGe heterostructures: Measurements and device implications", Applied Physics Letters, Volume 63, August 2, 1993, Number 5, pgs. 660-662.			
	CB	L. H. Jiang, "Electrical Properties of GeSi Surface- and Buried- Channel p-MOSFET's Fabricated by Ge Implantation", IEEE Electron Devices, Volume 43, January 1996, Number 1, pgs. 97-103.			
	CC	K. Ismail et al., "High Pole Mobility In SiGe Alloys For Device Applications", Applied Physics Letters, Volume 64, June 6, 1994, Number 23, pgs. 3124-3126.			
	CD	J. Welser et al., "Strain Dependence of the Performance Enhancement in Strained-Si n-MOSFETs", Electron Devices Meeting, 1994, pgs. 373-376.			

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<sup>1</sup>Applicant's unique citation designation number (optional). <sup>2</sup>Applicant is to place a check mark here if English language Translation is attached.

Examiner Signature	Date Considered
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